**IN THE CLAIMS:**

Please cancel claims 18-20 as shown in the following listing of claims:

1. (Previously presented) A method of manufacturing a semiconductor device said method forming metal wirings of a pattern connected through a conduction path to a control electrode on an insulating layer formed on a substrate, said method comprising:

forming a metal film;

forming, on said metal film, a hard mask with a film thickness of at least 150 nm but not greater than 300 nm, said hard mask containing a silicon inorganic insulating film, and said hard mask having said pattern; and

etching said metal film with said hard mask by use of an etching gas to form metal wiring of said pattern;

wherein, in said step of forming said metal wiring, the amount of electric charge in said metal film is decreased to reduce the occurrence of the breakdown and deterioration, caused by said electric charge flowing into said control electrode, of said insulating layer.

2. (Original) A method of manufacturing a semiconductor device according to claim 1, wherein said hard mask is made of silicon oxide.

3. (Original) A method of manufacturing a semiconductor device according to claim 1 or 2, wherein said metal film is at least one of an Al film and an Al alloy film.

4. (Original) A method of manufacturing a semiconductor device according to claim 1 or 2, wherein said metal film is at least one of a tungsten film and a copper alloy film.

5. (Previously presented) A method of manufacturing a semiconductor device according to claim 1, wherein said hard mask has a film thickness of at least 180 nm but not greater than 230 nm.

6. (Previously presented) A method of manufacturing a semiconductor device according to claim 1, wherein a barrier metal film is formed.

7. (Previously presented) A method of manufacturing a semiconductor device according to claim 6, further comprising etching said barrier metal film by use of said hard mask.

8. (Previously presented) A method of manufacturing a semiconductor device according to claim 1, wherein an antireflection film is provided between said metal film and said hard mask.

9. (Previously presented) A method of manufacturing a semiconductor device according to claim 8, further comprising etching said antireflection film by use of said hard mask.

10. (Original) A method of manufacturing a semiconductor device according to claim 1, wherein said etching gas contains Cl.

11. (Previously presented) A method of manufacturing a semiconductor device having metal wirings of a pattern, said method comprising:

forming, on an insulating layer, a control electrode for a metal-insulator-semiconductor type device;

forming a metal film connected through a conduction path to said control electrode;

forming, on said metal film, a hard. mask with a film thickness of at least 150 nm but not greater than 300 nm, said hard mask having said pattern and containing a silicon inorganic insulating film; and

etching said metal film with said hard mask by use of an etching gas to form metal wiring of said pattern.

12. (Previously presented) A method of manufacturing a semiconductor device according to claim 11, further comprising forming said insulating film prior to forming said control electrode on said insulating layer.

13. (Previously presented) A method of manufacturing a semiconductor device according to claim 11 or 12, further comprising forming a source and a drain for said metal-insulator-semiconductor device.

14. (Previously presented) A method of manufacturing a semiconductor device according to claim 11, wherein said hard mask is made of silicon oxide.

15. (Previously presented) A method of manufacturing a semiconductor device according to claim 11, wherein said hard mask has a film thickness of at least 180 nm but not greater than 230 nm.

16. (Previously presented) A method of manufacturing a semiconductor device according to claim 11, further comprising:

forming a barrier metal film prior to forming said metal film; and

etching said barrier metal film by use of said hard mask.

17. (Previously presented) A method of manufacturing a semiconductor device according to claim 11, further comprising:

forming an antireflection film on said metal film prior to forming said hard mask on said metal film; and

etching said antireflection film by use of said hard mask.

18-20. (Cancelled)